B1 end

wherein, the top surface of said silicide pad is formed above the top surface of said first interlayer insulating film.--

Amend claim 4 as follows:

--4. (amended) A method for manufacturing a semiconductor device, provided with a contact plug, which is formed by opening a contact hole through a first interlayer insulating film formed on a silicon substrate and filling the contact hole with silicon, comprising the steps of:

B2

forming a first insulating film on said silicon substrate;

forming said contact hole through said first interlayer insulating film;

filling said contact hole with a silicon plug; and

forming a silicide pad in a self-aligning manner with the silicon plug, the silicide pad having a larger diameter than that of said silicon plug.--

Amend claim 7 as follows:

--7. (amended) A structure of a semiconductor device, comprising:

a silicon substrate;

B3 cont'd

a first interlayer insulating film having a first surface connected to said substrate;

a polysilicon contact plug formed through said first interlayer insulating film having a top end surface and a top

side surface protruding from a second surface of said first insulating layer;

B3 and

a silicide pad formed covering said top end surface and said top side surface of said polysilicon contact plug in a self-aligning manner with said polysilicon contact plug and said silicide pad having a diameter which is larger than a diameter of the polysilicon contact plug, said silicide pad being above said second surface of said first interlayer insulating film.--

Amend claim 10 as follows:

--10. (amended) The structure of a semiconductor device according to claim 7, further comprising:

a second interlayer insulating film on the second surface of said first interlayer insulating film and on said silicide pad;

B4 cont'd

a tungsten plug through said second interlayer insulating film and aligned with the polysilicon contact plug, said tungsten plug contacting said silicide pad; and

an aluminum copper alloy connected to said second interlayer insulating film and said tungsten plug.--

Amend claim 11 as follows:

--11. (amended) A structure of a semiconductor device, comprising:

a silicon substrate;

a first interlayer insulating film having a first surface on the substrate;

a polysilicon contact plug through said first interlayer insulating film;

a silicide pad formed on a first surface of said polysilicon contact plug in a self-aligning manner with said polysilicon contact plug and having a diameter which is larger than the polysilicon contact plug, a first surface of said silicide pad being above a second surface of said interlayer insulating film; and

B4 contd

a second interlayer insulating film on said first interlayer insulating film on said silicide pad.--

Amend claim 12 as follows:

--12. (amended) A structure of a semiconductor device according to claim 11, further comprising:

an upper plug on the polysilicon plug and through said second interlayer insulating film and aligned with the polysilicon contact plug;

and a conductive film connected to said second interlayer insulating film and said upper plug.--

Amend claim 13 as follows:

--13. (amended) A method for manufacturing a semiconductor device, comprising the steps of:

forming a silicon substrate;

forming a first interlayer insulating film above the silicon substrate;

forming a first contact hole though the first interlayer insulating film;

forming a polysilicon layer on the first interlayer insulating film, the polysilicon layer filling the contact hole and forming a polysilicon plug; and

forming a silicide pad on the polysilicon plug in a self-aligning manner with the polysilicon plug, the silicide pad having a diameter larger than a diameter of the polysilicon plug, a first surface of the silicide pad being disposed above an upper surface of the first interlayer insulating film.--

Amend claim 16 as follows:

--16. (amended) The method for manufacturing a semiconductor device according to claim 13, further comprising the steps of:

forming a second interlayer insulating film on the first interlayer insulating film and on the silicide pad;

forming a second contact hole through the second interlayer insulating film, the second contact hole extending to the silicide pad;

forming a titanium nitrite layer on walls of the second contact hole and on the silicide pad;

filling the contact hole with tungsten to form a tungsten plug, the tungsten plug contacting the titanium nitrite

layer and being connected to the polysilicon plug through the silicide pad and being aligned with the polysilicon plug; and

forming a tungsten layer on the second interlayer insulating film and contacting the tungsten plug.--

Amend claim 17 as follows:

--17. (amended) A method for manufacturing a semiconductor device, comprising the steps of:

forming a silicon substrate;

forming a first interlayer insulating film above the silicon substrate;

B5 cont'd

forming a first contact hole through the first interlayer insulating film;

forming a polysilicon layer on the first interlayer insulating film, the polysilicon layer filling the contact hole and forming a polysilicon plug;

forming a silicide pad in a self-aligning manner with the polysilicon plug, the silicide pad having a diameter larger than a diameter of the polysilicon plug, a first surface of the silicide pad being disposed above an upper surface of the first interlayer insulating film

forming a second interlayer insulating film on the first interlayer insulating film and on the silicide pad;

forming a second contact hole through the second interlayer insulating film, the second contact hole extending to the silicide pad;